

## Small Signal MOSFET Transistor

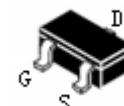
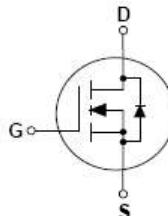
**2N7002T**

### FEATURES

- Low on-resistance.
- Low gate threshold voltage.
- Low input capacitance.
- Fast switching speed.
- Low input/output leakage.



Lead-free



**SOT-523**

### APPLICATIONS

- N-channel enhancement mode effect transistor.
- Switching application.

### ORDERING INFORMATION

Type No.	Marking	Package Code
2N7002T	72	SOT-523

### MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V <sub>DSS</sub>	Drain-Source voltage	60	V
V <sub>DGR</sub>	Drain-Gate voltage( $R_{GS} \leq 1M\Omega$ )	60	V
V <sub>GSS</sub>	Gate -Source voltage - continuous -Non Repetitive ( $t_p < 50\mu s$ )	$\pm 20$ $\pm 40$	V
I <sub>D</sub>	Maximum Drain current -continuous -Pulsed	115 800	mA
P <sub>D</sub>	Power Dissipation	150	mW
R <sub>θJA</sub>	Thermal resistance,Junction-to-Ambient	833	°C/W
T <sub>J</sub> , T <sub>stg</sub>	Junction and Storage Temperature	-55 to +150	°C

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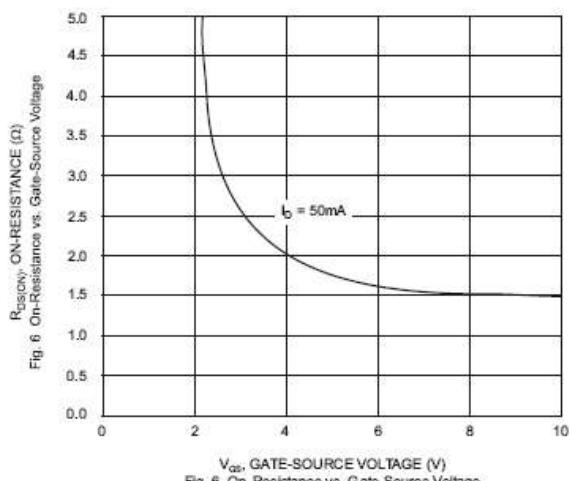
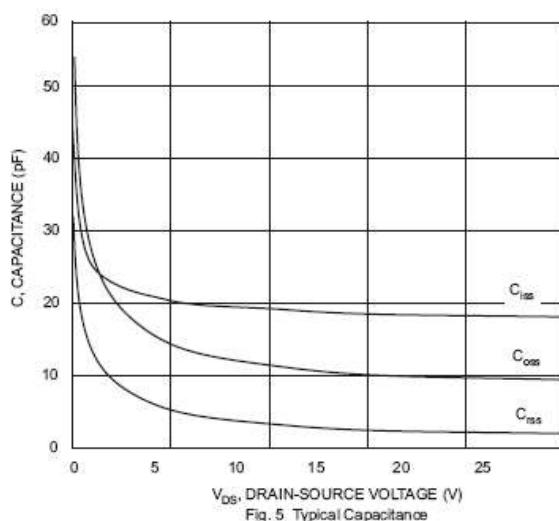
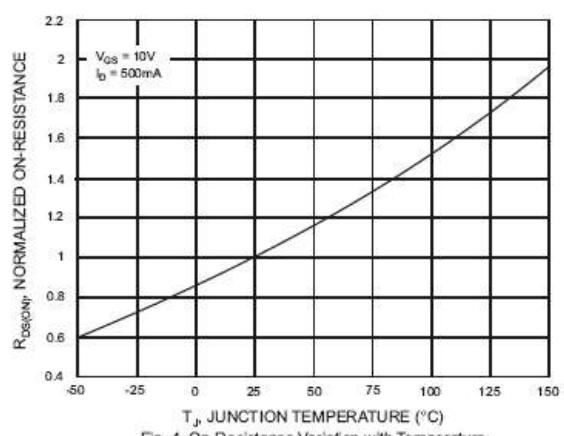
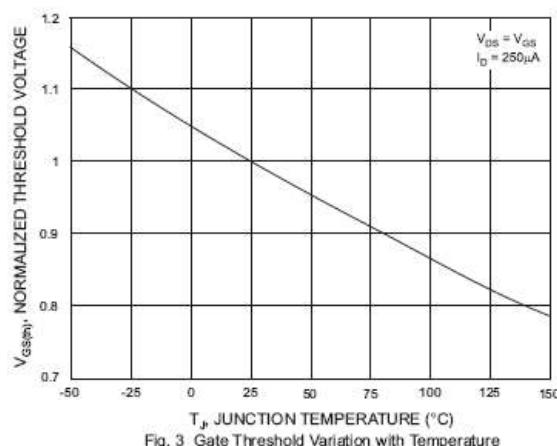
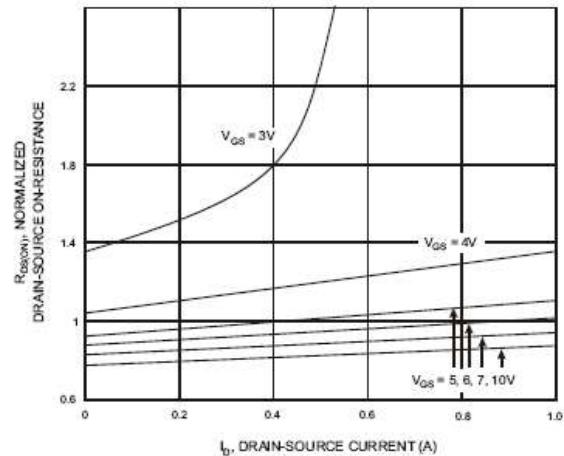
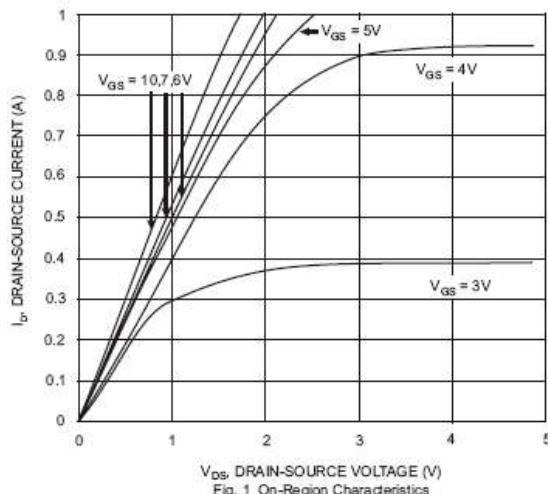
### ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ C$ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=10\mu A$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1		2	
Gate-body Leakage	$I_{GSS}$	$V_{DS}=0V, V_{GS}=20V$ $V_{DS}=0V, V_{GS}=-20V$			10 -10	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$			1	$\mu A$
		$V_{DS}=60V, V_{GS}=0V, T_j=125^\circ C$			500	
On-state Drain Current	$I_{D(ON)}$	$V_{GS}=10V, V_{DS}=7.5V$	0.5	1.0		A
Forward transconductance	$g_{FS}$	$V_{DS}=10V, I_D=200mA$	80			mS
Static drain-Source on-resistance	$R_{DS(ON)}$	$V_{GS}=5.0V, I_D=50mA$		2	7.5	$\Omega$
Input capacitance	$C_{ISS}$	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$		22	50	pF
Output capacitance	$C_{OSS}$			11	25	
Reverse transfer capacitance	$C_{RSS}$			2	5	
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=30V, I_D=0.2A,$ $R_L=150\Omega, V_{GS}=10V,$ $R_{GEN}= 25\Omega$		7.0	20	ns
Turn-Off Delay Time	$t_{D(OFF)}$			11	20	ns

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TYPICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified



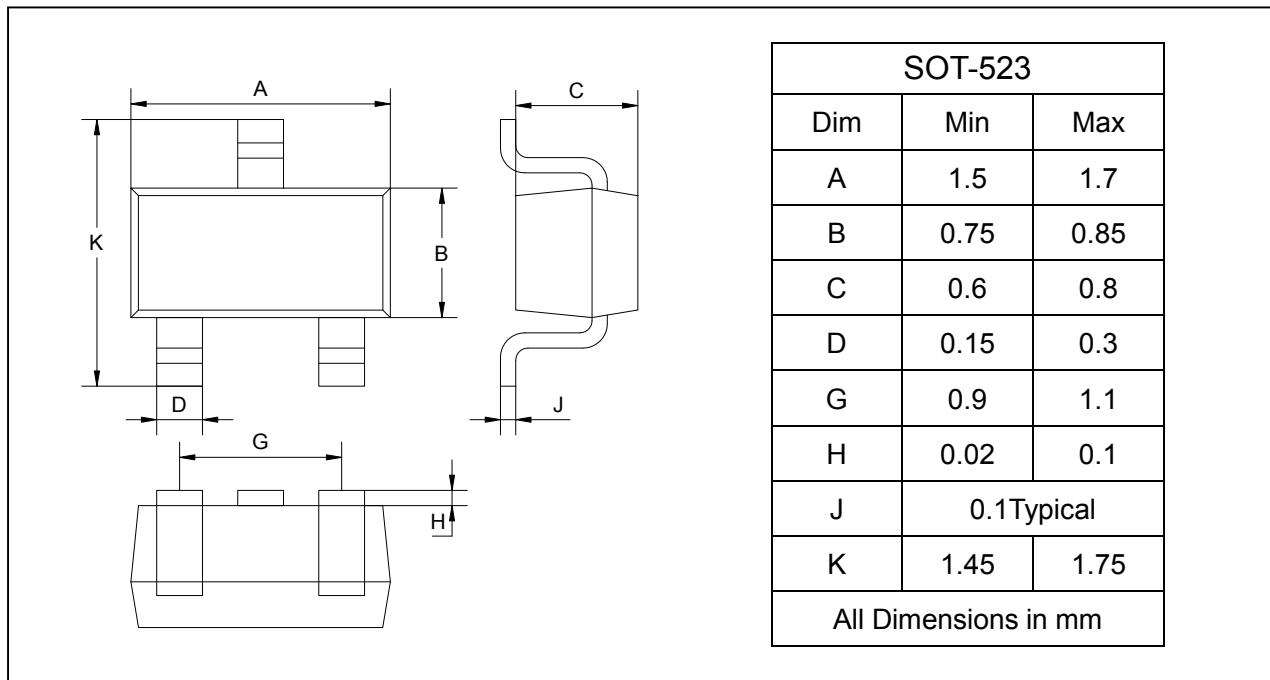
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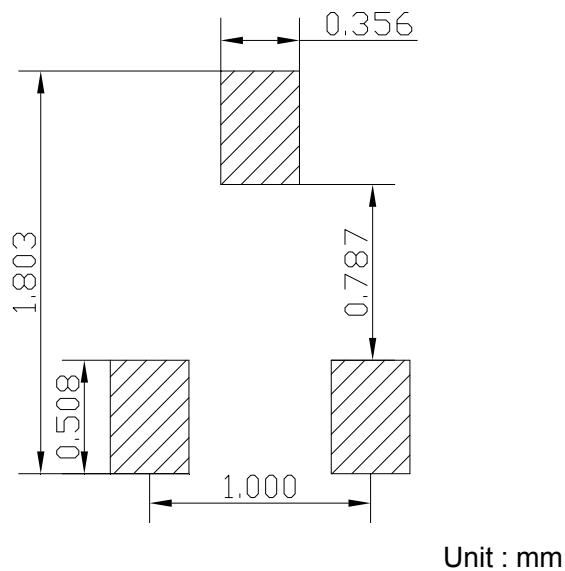
### PACKAGE OUTLINE

Plastic surface mounted package

SOT-523



### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

Device	Package	Shipping
2N7002T	SOT-523	3000/Tape&Reel